

ABSTRACT OF THE DISCLOSURE (Fig. 1)

**SEMICONDUCTOR MEMORY DEVICE
AND DATA PROCESSING DEVICE USING SAME**

In the peripheral circuit of a static RAM comprised by memory cells (1) of the polysilicon high resistance type, is provided a word line voltage transformation circuit (50) which sets the potential of a selected word line (WL) during writing operation to be the potential V_{WOL} , the value of which is higher than that of the supplied potential V_{DD} . The word line voltage transformation circuit comprises a ring-oscillator circuit, a transformation timing signal generating circuit, a step-up gate control signal generating circuit, a stepped-up potential generating circuit, a word line supplied potential mixing circuit, and a word line potential supply control circuit.